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## 1. General description

NPN high-voltage low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor in a SOT89 (SC-62) medium power and flat lead Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV9115X.

### 2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- AEC-Q101 qualified
- Medium power SMD plastic package

## 3. Applications

- LED driver for LED chain module
- LCD backlighting
- High Intensity Discharge (HID) front lighting
- Automotive motor management
- Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	150	V
I <sub>C</sub>	collector current		-	-	1	Α
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 10 V; $I_{C}$ = 50 mA; $T_{amb}$ = 25 °C	100	250	-	





150 V, 1 A NPN high-voltage low VCEsat (BISS) transistor

# 5. Pinning information

### Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		2
2	С	collector		3—
3	В	base	3 2 1 SOT89	1 sym042

# 6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBHV8115X	SOT89	plastic surface-mounted package; die pad for good heat transfer; 3 leads	SOT89		

# 7. Marking

Table 4. Marking codes

Type number	Marking code
	[1]
PBHV8115X	%4F

[1] % = placeholder for manufacturing site code

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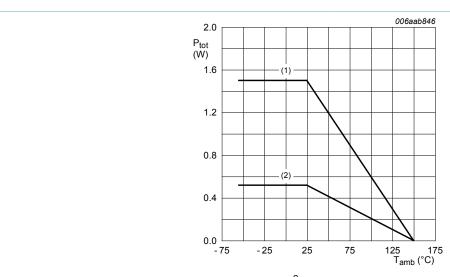
## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	400	V
$V_{CEO}$	collector-emitter voltage	open base		-	150	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	6	V
I <sub>C</sub>	collector current			-	1	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	2	Α
I <sub>BM</sub>	peak base current			-	400	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	0.52	W
			[2]	-	1.5	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



- (1) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (2) FR4 PCB, standard footprint

Fig. 1. Power derating curves

150 V, 1 A NPN high-voltage low VCEsat (BISS) transistor

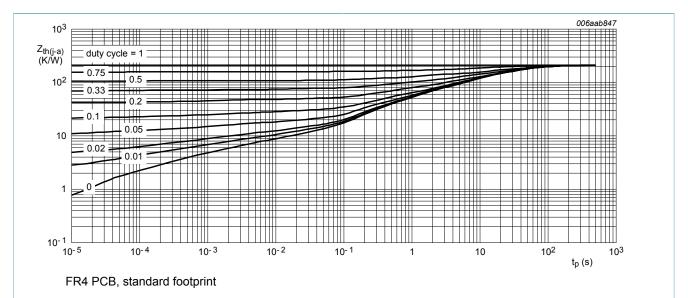
### Thermal characteristics

Table 6. Thermal characteristics

PBHV8115X

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
( 2)	thermal resistance from junction to ambient	in free air	[1]	-	-	240	K/W
			[2]	-	-	83	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	20	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 2.

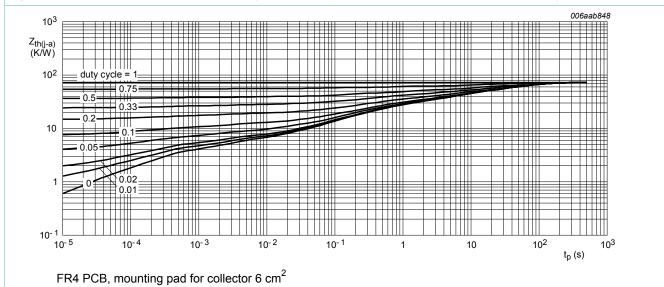


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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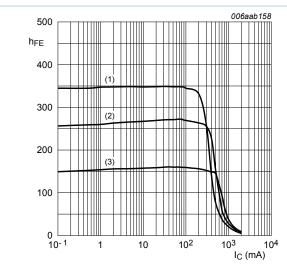
150 V, 1 A NPN high-voltage low VCEsat (BISS) transistor

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 120 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 120 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	10	μA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 120 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 4 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 10 V; $I_{C}$ = 50 mA; $T_{amb}$ = 25 °C	100	250	-	
		$V_{CE}$ = 10 V; $I_{C}$ = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	100	250	-	
		$V_{CE} = 10 \text{ V; } I_{C} = 0.5 \text{ A; pulsed;}$ $t_{p} \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	50	160	-	
		$V_{CE} = 10 \text{ V; } I_{C} = 1 \text{ A; } t_{p} \le 300  \mu\text{s;}$ $\delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	10	30	-	
V <sub>CEsat</sub>	collector-emitter	I <sub>C</sub> = 100 mA; I <sub>B</sub> = 20 mA; T <sub>amb</sub> = 25 °C	-	33	50	mV
	saturation voltage	I <sub>C</sub> = 100 mA; I <sub>B</sub> = 10 mA; T <sub>amb</sub> = 25 °C	-	40	60	mV
		$I_C$ = 1 A; $I_B$ = 0.2 A; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	225	350	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_{C}$ = 1 A; $I_{B}$ = 200 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	1.1	1.2	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = 6 V; I <sub>C</sub> = 0.5 A; I <sub>Bon</sub> = 0.1 A;	-	7	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = -0.1 A; T <sub>amb</sub> = 25 °C	-	565	-	ns
t <sub>on</sub>	turn-on time	_	-	572	-	ns
t <sub>s</sub>	storage time	_	-	1530	-	ns
t <sub>f</sub>	fall time		-	700	-	ns
t <sub>off</sub>	turn-off time		-	2230	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = 10 V; $I_{C}$ = 10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	30	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = 20 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	5.7	-	pF
Ce	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_C = 0 \text{ A}; i_c = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	150	-	pF

### 150 V, 1 A NPN high-voltage low VCEsat (BISS) transistor



$$V_{CE} = 10 \text{ V}$$

(1) 
$$T_{amb}$$
 = 100 °C

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = -55 °C$$

Fig. 4. DC current gain as a function of collector current; typical values

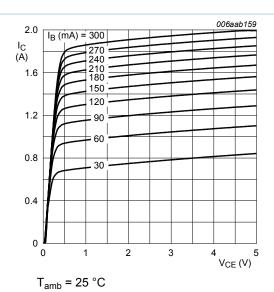
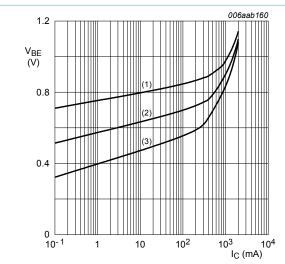


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



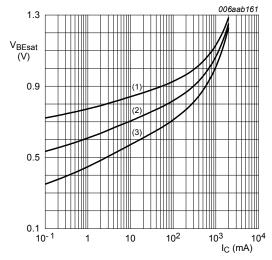
$$V_{CE} = 10 V$$

(1) 
$$T_{amb} = -55$$
 °C

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



$$I_C/I_B = 5$$

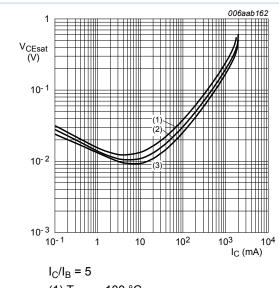
(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

### 150 V, 1 A NPN high-voltage low VCEsat (BISS) transistor

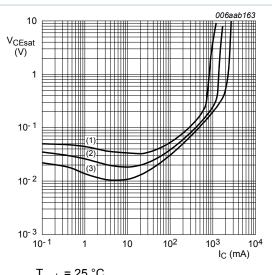


(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = -55 °C$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



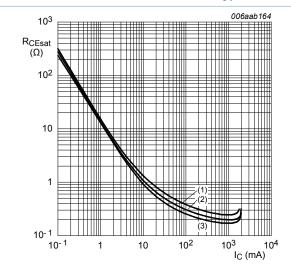
$$T_{amb}$$
 = 25 °C

(1) 
$$I_C/I_B = 20$$

(2) 
$$I_C/I_B = 10$$

(3) 
$$I_C/I_B = 5$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



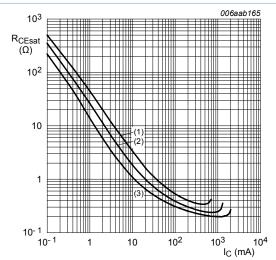
$$I_C/I_B = 5$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values



(1) 
$$I_C/I_B = 20$$

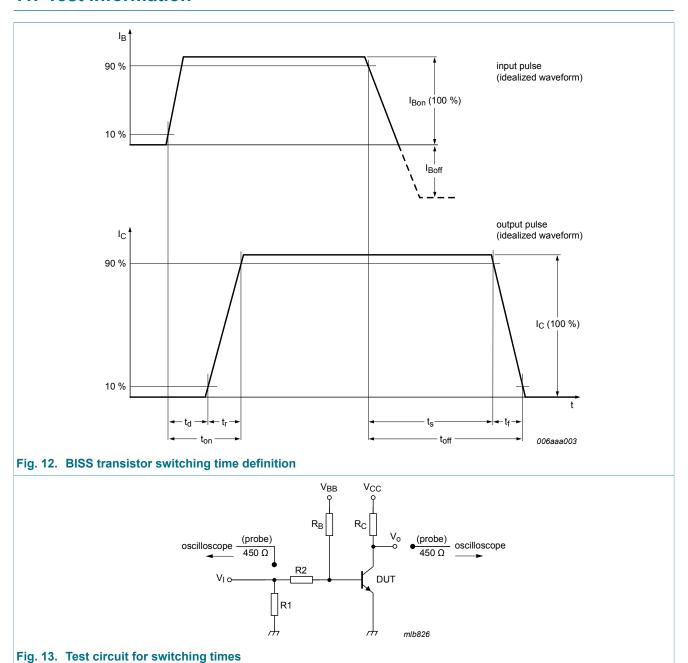
(2) 
$$I_C/I_B = 10$$

(3) 
$$I_C/I_B = 5$$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

150 V, 1 A NPN high-voltage low VCEsat (BISS) transistor

### 11. Test information



### 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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## 12. Package outline

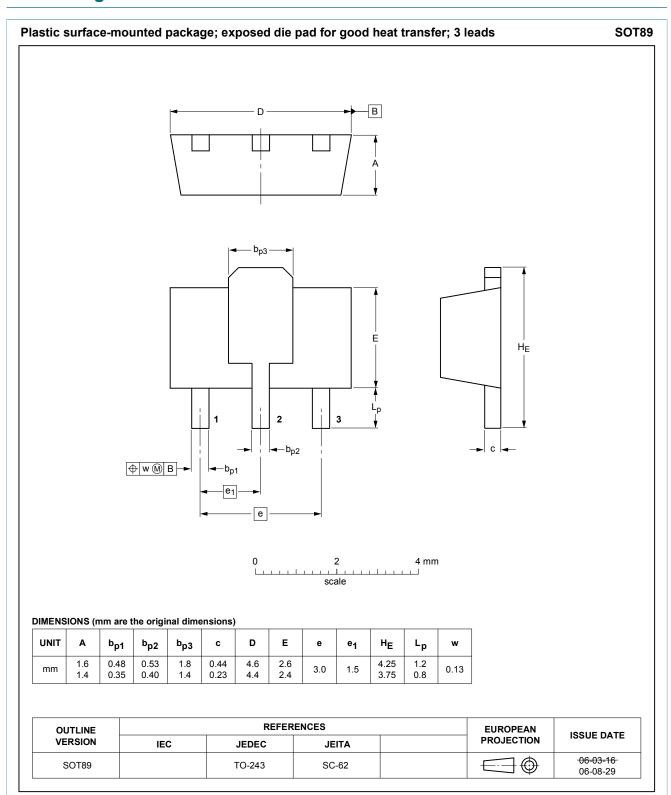


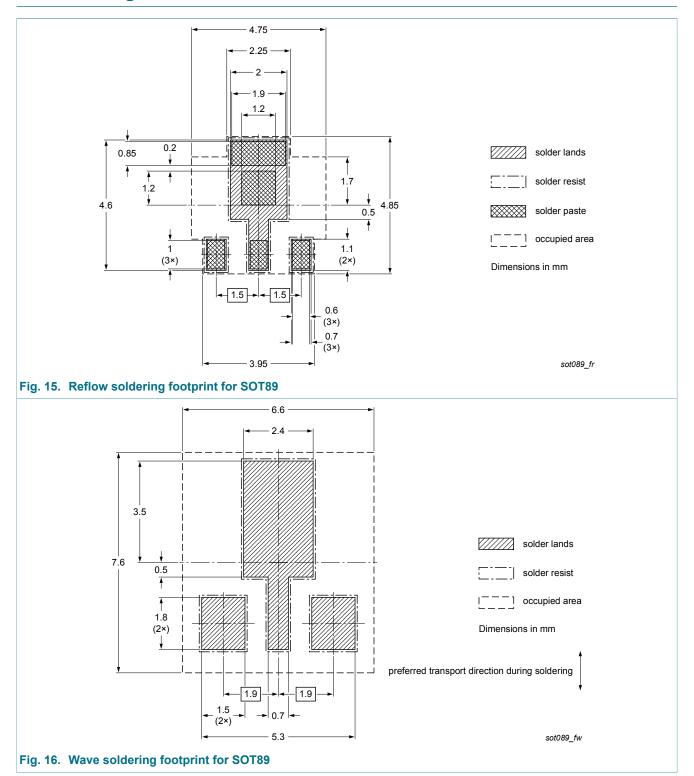
Fig. 14. Package outline SOT89

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## 13. Soldering



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# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV8115X v.1	20131209	Product data sheet	-	-

#### 150 V, 1 A NPN high-voltage low VCEsat (BISS) transistor

## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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### 150 V, 1 A NPN high-voltage low VCEsat (BISS) transistor

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